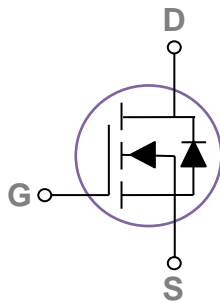
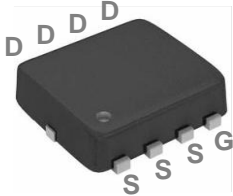


### General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
30V	6mΩ	60A

### PPAK3x3 Pin Configuration



### Features

- 30V,60A,  $R_{DS(ON)} = 6m\Omega @ V_{GS} = 10V$
- Improved  $dv/dt$  capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

### Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2<sup>nd</sup> SR

### Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_c=25^\circ C$ )	60	A
	Drain Current – Continuous ( $T_c=100^\circ C$ )	38	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	240	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	88	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	42	A
$P_D$	Power Dissipation ( $T_c=25^\circ C$ )	45	W
	Power Dissipation – Derate above $25^\circ C$	0.36	W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	2.8	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Static State Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.04	---	V/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>3</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	---	4.8	6	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	6.7	9	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.6	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4	---	mV/°C
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =10A	---	23	---	S

**Dynamic Characteristics**

Q <sub>g</sub>	Total Gate Charge <sup>3, 4</sup>	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	---	11.1	18	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>3, 4</sup>		---	1.85	3.8	
Q <sub>gd</sub>	Gate-Drain Charge <sup>3, 4</sup>		---	6.8	12	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>3, 4</sup>	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =15A	---	7.5	14	ns
T <sub>r</sub>	Rise Time <sup>3, 4</sup>		---	14.5	28	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>3, 4</sup>		---	35.2	67	
T <sub>f</sub>	Fall Time <sup>3, 4</sup>		---	9.6	18	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, F=1MHz	---	1210	1800	pF
C <sub>oss</sub>	Output Capacitance		---	190	280	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	100	150	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	2.5	5	Ω

**Guaranteed Avalanche Energy**

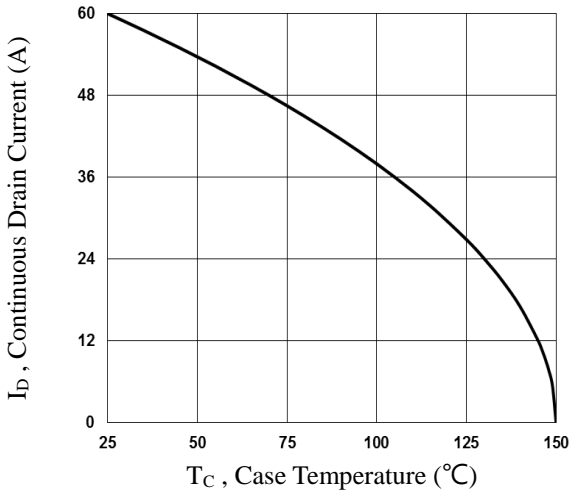
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy	V <sub>DD</sub> =25V, L=0.1mH, I <sub>AS</sub> =20A	20	---	---	mJ

**Drain-Source Diode Characteristics**

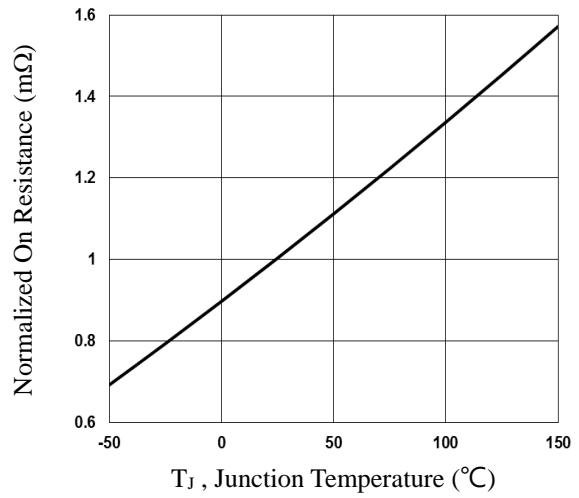
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	60	A
I <sub>SM</sub>	Pulsed Source Current <sup>3</sup>		---	---	240	A
V <sub>SD</sub>	Diode Forward Voltage <sup>3</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, di/dt=100A/μs	---	---	---	ns
Q <sub>rr</sub>	Reverse Recovery Charge	T <sub>J</sub> =25°C	---	---	---	nC

Note :

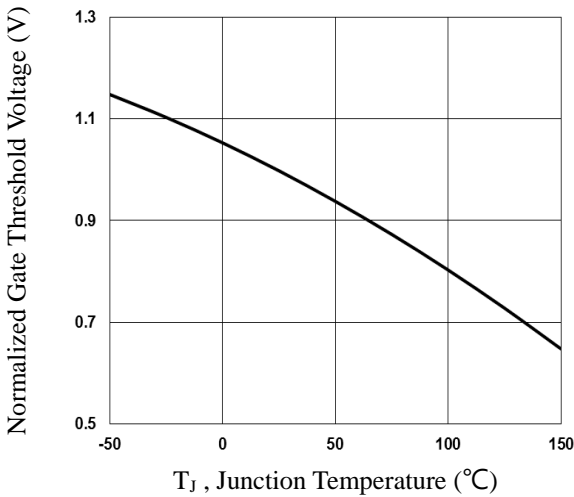
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=42A., R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.



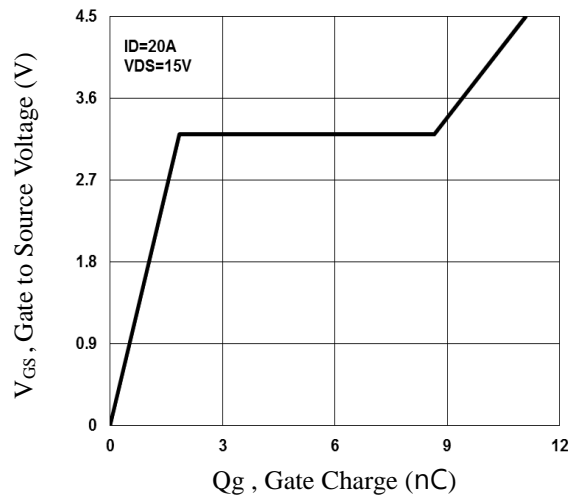
**Fig.1 Continuous Drain Current vs. T<sub>c</sub>**



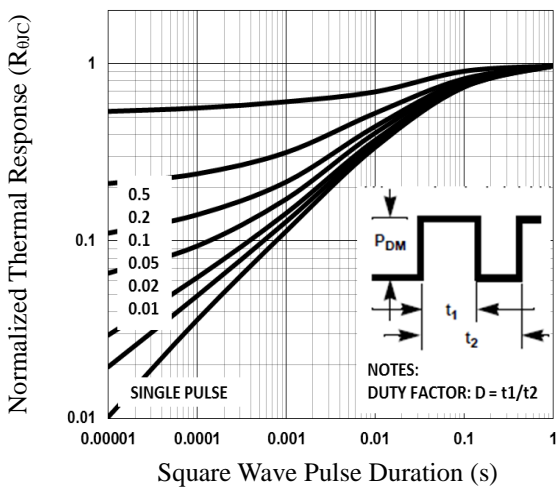
**Fig.2 Normalized R<sub>DS(on)</sub> vs. T<sub>j</sub>**



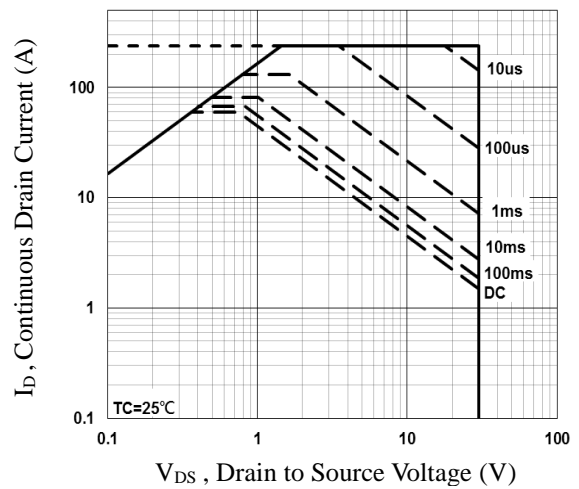
**Fig.3 Normalized V<sub>th</sub> vs. T<sub>j</sub>**



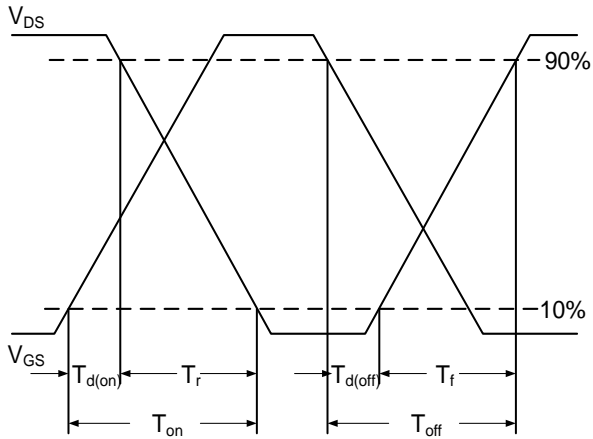
**Fig.4 Gate Charge Waveform**



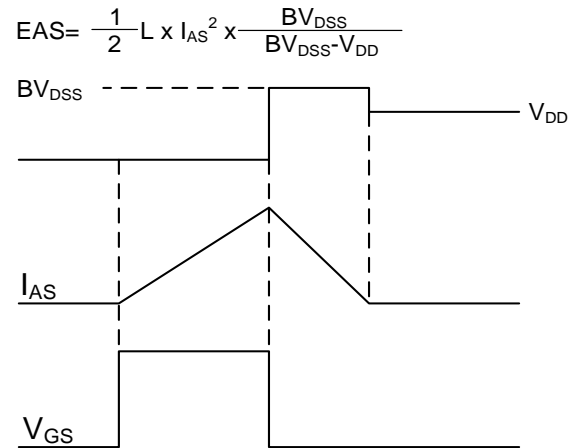
**Fig.5 Normalized Transient Impedance**



**Fig.6 Maximum Safe Operation Area**

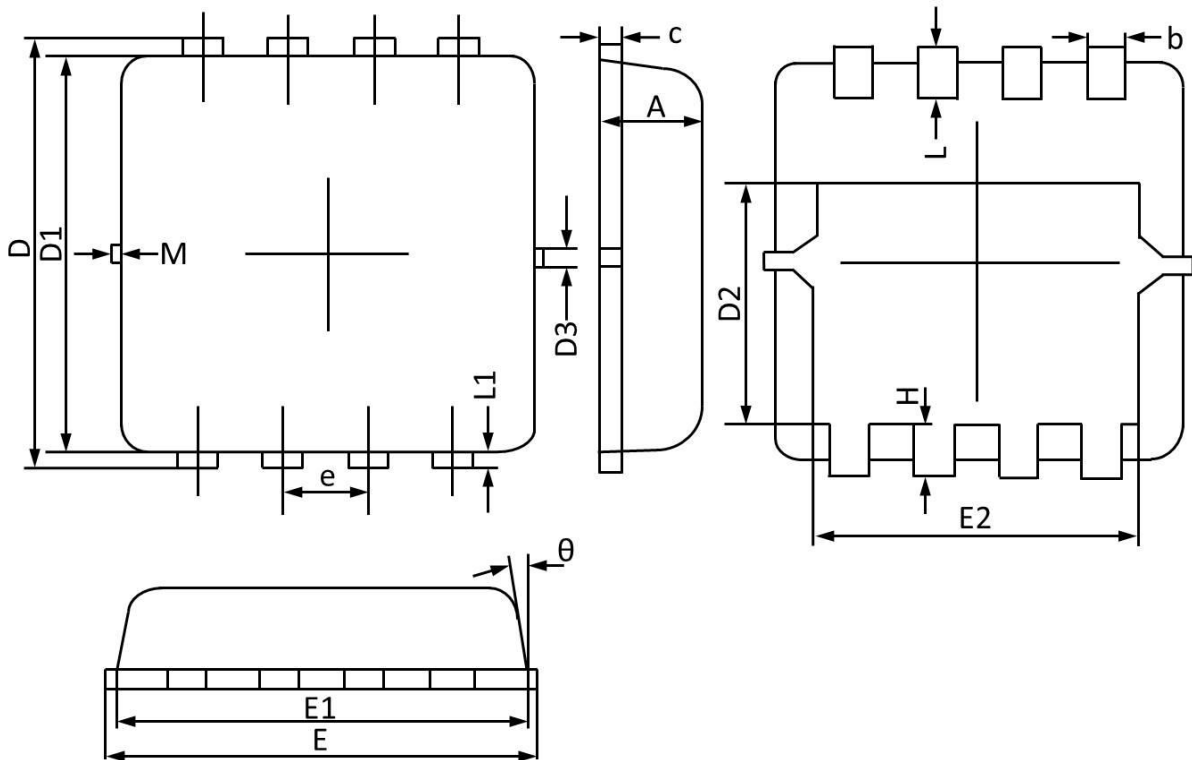


**Fig.7 Switching Time Waveform**



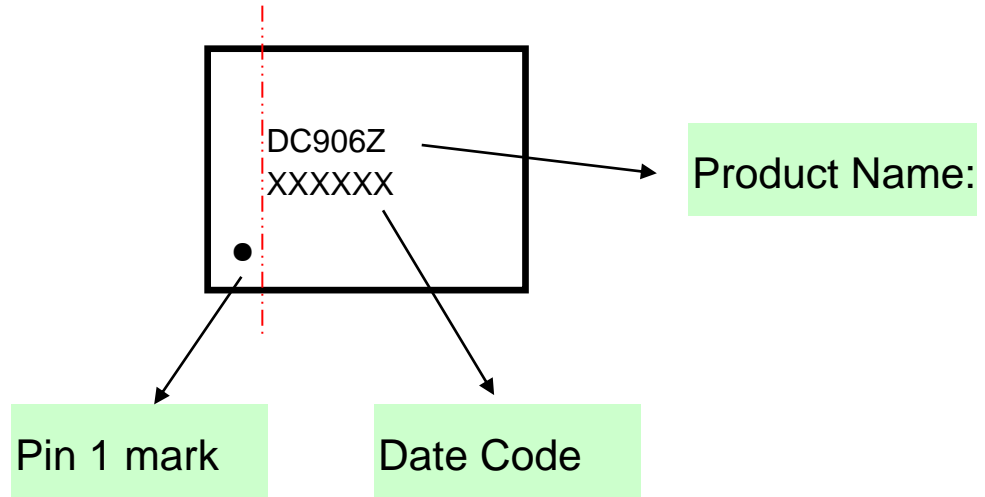
**Fig.8 EAS Waveform**

### PPAK3x3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
b	0.250	0.350	0.010	0.013
c	0.100	0.250	0.004	0.009
D	3.250	3.450	0.128	0.135
D1	3.000	3.200	0.119	0.125
D2	1.780	1.980	0.070	0.077
D3	0.130 REF		0.005 REF	
E	3.200	3.400	0.126	0.133
E1	3.000	3.200	0.119	0.125
E2	2.390	2.590	0.094	0.102
e	0.650 BSC		0.026 BSC	
H	0.300	0.500	0.011	0.019
L	0.300	0.500	0.011	0.019
L1	0.130 REF		0.005 REF	
θ	0°	12°	0°	12°
M	0.150 REF		0.006 REF	

## TOP MARKING INFORMATION



D/C		
X	X	XXXX
第1碼	第2碼	第3-6碼
西元年西元年	生產週別	流水號
P 2018 上半年	1-26:A-Z	
Q 2018 下半年	27-52:A-Z	
R: 2019 上半年	1-26:A-Z	
S: 2019 下半年	27-52:A-Z	